

present application describes a technique of manufacturing a semiconductor device. A dopant impurity is introduced into a crystalline semiconductor film formed on an insulating surface, through the insulating film. The insulating film is formed on the crystalline semiconductor film ion doping. In one embodiment, a peak of the concentration profile of the dopant impurity is located in the insulating film; see claims 1, 43, and 65. In another embodiment, a peak of a concentration profile of the dopant impurity is located above the insulating surface; see claims 22, 52, and 74. This is supported at least in FIG. 5.

U.S. Patent No. 5,488,000 to Zhang is used for rejecting the claims. However, it is respectfully suggested that Zhang does not teach that the concentration profile of a dopant impurity is as within the independent claims as claimed. For these reasons, it is respectfully suggested that the rejection based on Zhang does not meet the Patent Office's burden of providing a *prima facie* showing of unpatentability.

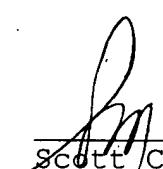
The rejection also contends that since Zhang uses the same steps as the present invention, this creates the same results. However, it is respectfully suggested that this contention is based on hindsight and not on factual data. The operation of forming silicon oxide prior to and during ion implantation has nothing to do with the concentration profile of the dopant

impurity, as claimed. For these reasons, therefore, it is respectfully suggested that all of these claims should be in condition for allowance. A formal notice of allowance is respectfully solicited.

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Respectfully submitted,

Date: 1/30/02



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